



PSMN3R7-25YLC

N-channel 25 V 3.9 m Ω logic level MOSFET in LPAK using NextPower technology

Rev. 01 — 2 May 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD and QOSS for high system efficiencies at low and high loads

1.3 Applications

- DC-to-DC converters
- Load switching
- Power OR-ing
- Server power supplies
- Sync rectifier

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$25\text{ }^{\circ}\text{C} \leq T_j \leq 175\text{ }^{\circ}\text{C}$	-	-	25	V
I_D	drain current	$T_{mb} = 25\text{ }^{\circ}\text{C}$; $V_{GS} = 10\text{ V}$; see Figure 1	-	-	97	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ }^{\circ}\text{C}$; see Figure 2	-	-	64	W
T_j	junction temperature		-55	-	175	$^{\circ}\text{C}$
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}$; $I_D = 20\text{ A}$; $T_j = 25\text{ }^{\circ}\text{C}$; see Figure 12	-	4.25	5.1	m Ω
		$V_{GS} = 10\text{ V}$; $I_D = 20\text{ A}$; $T_j = 25\text{ }^{\circ}\text{C}$; see Figure 12	-	3.3	3.9	m Ω

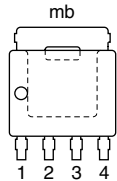
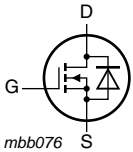


Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 4.5\text{ V}; I_D = 20\text{ A};$	-	3	-	nC
$Q_{G(\text{tot})}$	total gate charge	$V_{DS} = 12\text{ V};$ see Figure 14 ; see Figure 15	-	10.1	-	nC

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

SOT669 (LPAK; Power-SO8)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN3R7-25YLC	LPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PSMN3R7-25YLC	3C725L

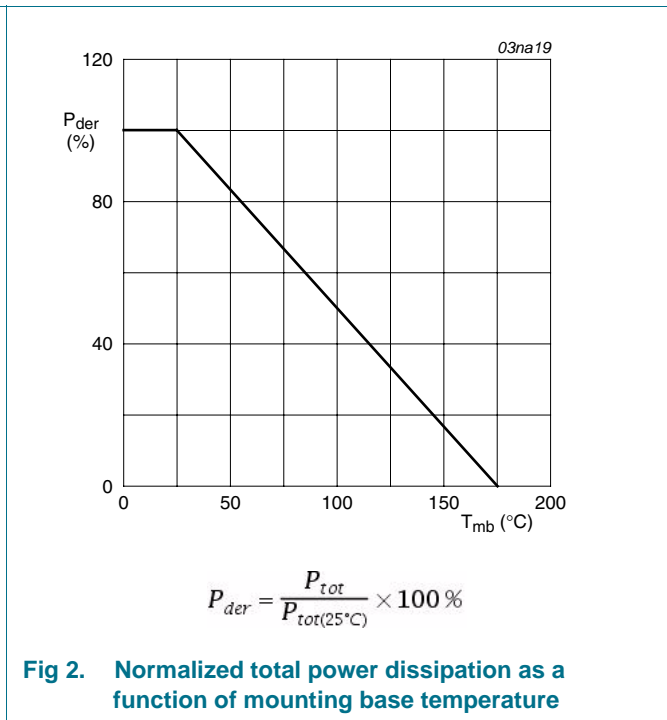
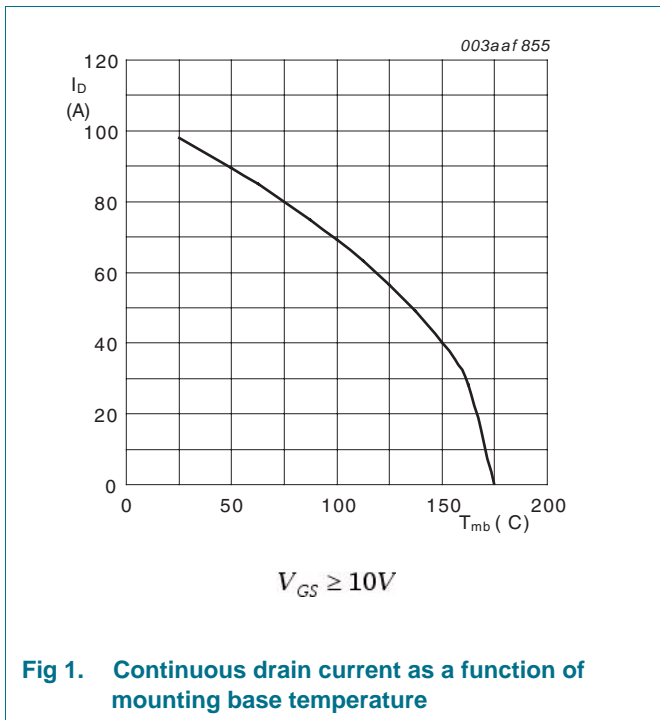
[1] % = placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	25	V
V _{DGR}	drain-gate voltage	25 °C ≤ T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	25	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see Figure 1	-	97	A
		V _{GS} = 10 V; T _{mb} = 100 °C; see Figure 1	-	68	A
I _{DM}	peak drain current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; see Figure 4	-	387	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2	-	64	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	310	-	V
Source-drain diode					
I _S	source current	T _{mb} = 25 °C	-	58	A
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C	-	387	A
Avalanche ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V _{GS} = 10 V; T _{j(init)} = 25 °C; I _D = 98 A; V _{sup} ≤ 25 V; unclamped; R _{GS} = 50 Ω; see Figure 3	-	24	mJ



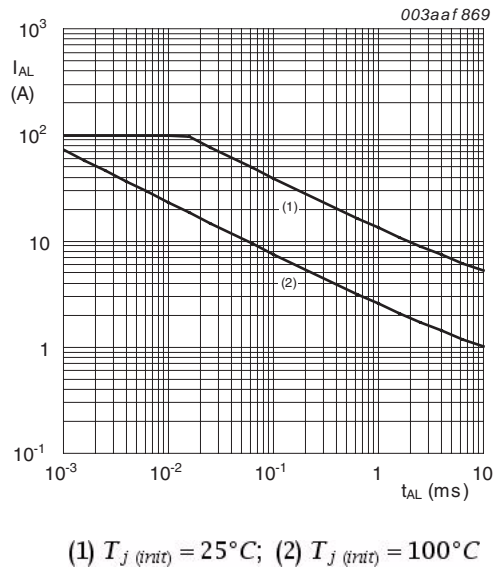


Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

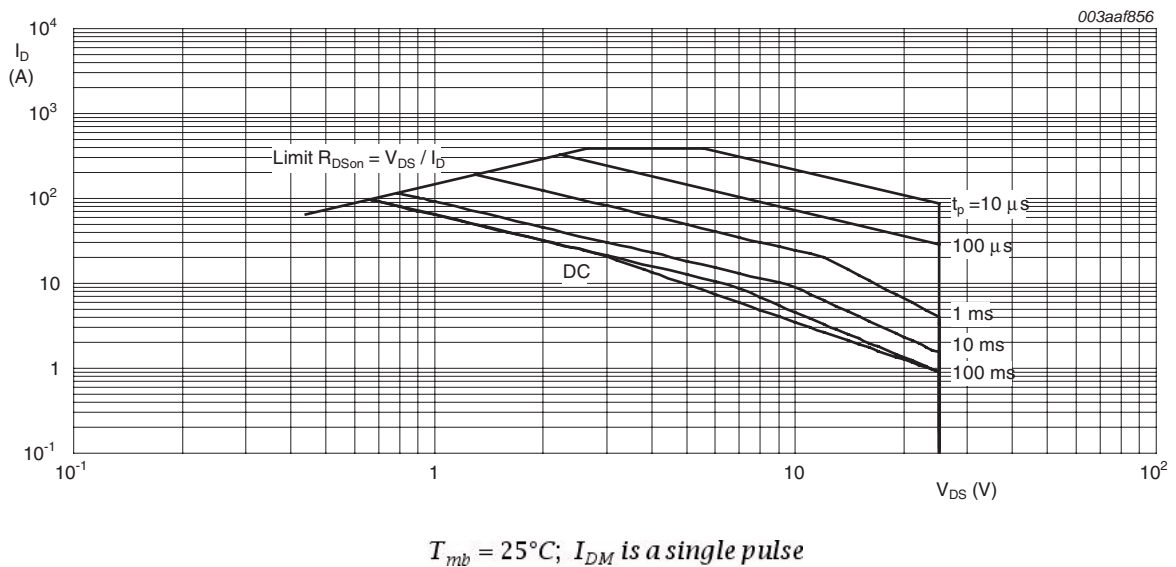


Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	2.14	2.34	K/W

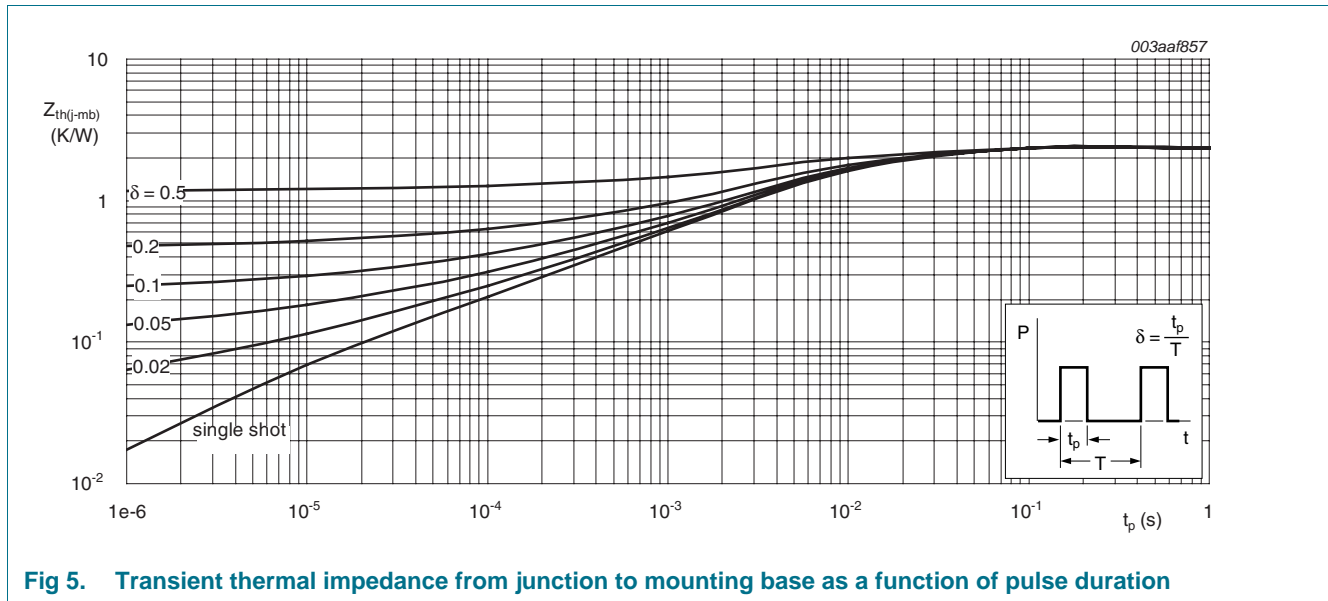


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	25	-	-	V
		$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	22.5	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 10 ; see Figure 11	1.05	1.54	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ }^\circ\text{C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C}$	-	-	2.25	V
I_{DSS}	drain leakage current	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	-	1	μA
		$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ }^\circ\text{C}$	-	-	100	μA
I_{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	-	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	-	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 12	-	4.25	5.1	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 150 \text{ }^\circ\text{C};$ see Figure 12 ; see Figure 13	-	-	8.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 12	-	3.3	3.9	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 150 \text{ }^\circ\text{C};$ see Figure 12 ; see Figure 13	-	-	6.3	mΩ
R_G	gate resistance	$f = 1 \text{ MHz}$	-	1.7	3.4	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 20 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 ; see Figure 15	-	21.6	-	nC
		$I_D = 20 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$ see Figure 14 ; see Figure 15	-	10.1	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	20.3	-	nC
Q_{GS}	gate-source charge	$I_D = 20 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$ see Figure 14 ; see Figure 15	-	3.2	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	2.1	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	1.1	-	nC
Q_{GD}	gate-drain charge		-	3	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 20 \text{ A}; V_{DS} = 12 \text{ V};$ see Figure 14 ; see Figure 15	-	2.62	-	V
C_{iss}	input capacitance	$V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 16	-	1585	-	pF
C_{oss}	output capacitance		-	370	-	pF
C_{riss}	reverse transfer capacitance		-	133	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 12 \text{ V}; R_L = 0.5 \text{ } \Omega; V_{GS} = 4.5 \text{ V};$ $R_{G(ext)} = 4.7 \text{ } \Omega$	-	16.6	-	ns
t_r	rise time		-	16.3	-	ns
$t_{d(off)}$	turn-off delay time		-	26	-	ns
t_f	fall time		-	10.7	-	ns

Table 7. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Q_{oss}	output charge	$V_{GS} = 0\text{ V}; V_{DS} = 12\text{ V}; f = 1\text{ MHz}; T_j = 25\text{ °C}$	-	8	-	nC
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 20\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ °C};$ see Figure 17	-	0.8	1.1	V
t_{rr}	reverse recovery time	$I_S = 20\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s};$	-	23	-	ns
Q_r	recovered charge	$V_{GS} = 0\text{ V}; V_{DS} = 12\text{ V}$	-	14	-	nC
t_a	reverse recovery rise time	$V_{GS} = 0\text{ V}; I_S = 20\text{ A};$	-	13.5	-	ns
t_b	reverse recovery fall time	$di_S/dt = -100\text{ A}/\mu\text{s}; V_{DS} = 12\text{ V};$ see Figure 18	-	9.5	-	ns

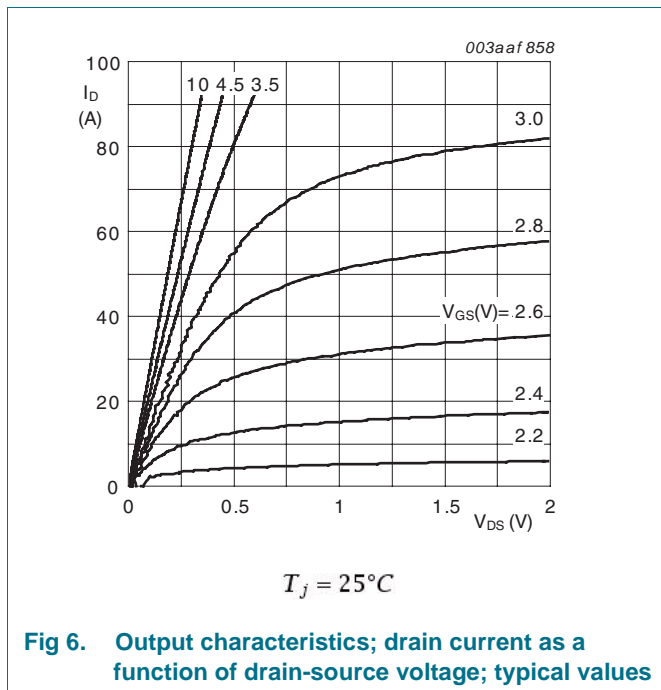


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

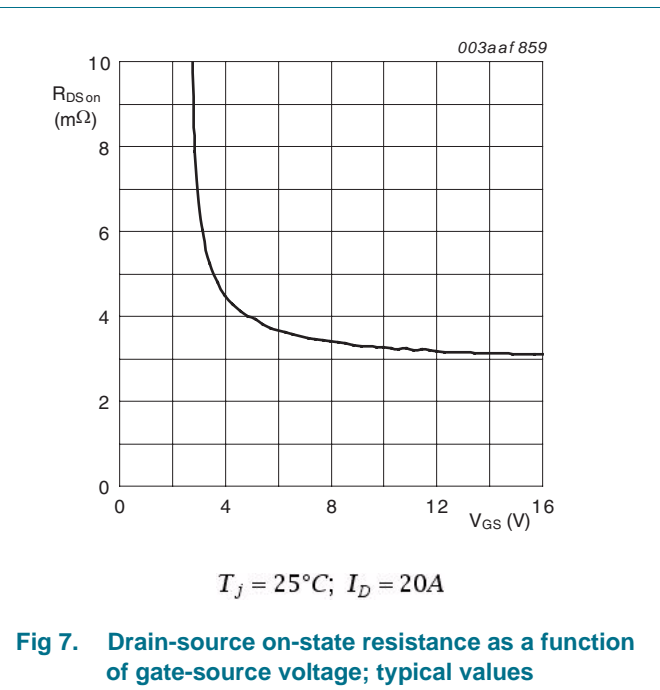
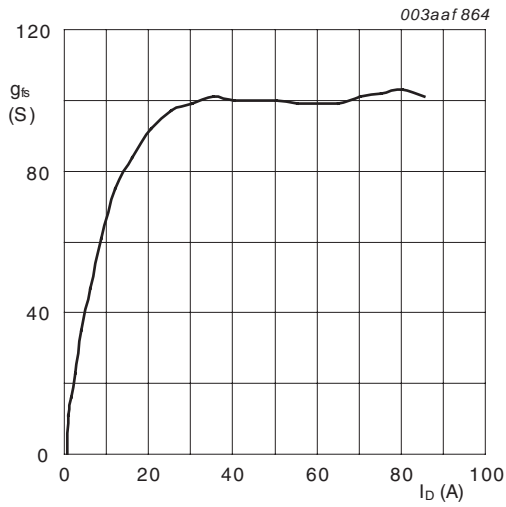
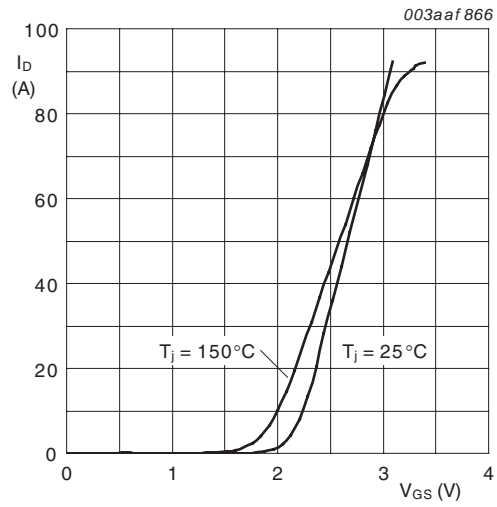


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



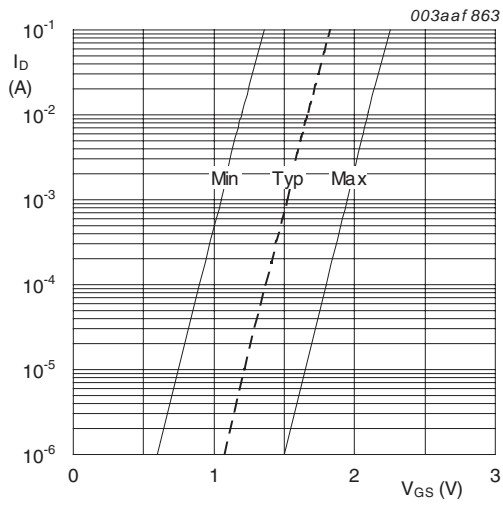
$T_j = 25^\circ\text{C}; V_{DS} = 10\text{V}$

Fig 8. Forward transconductance as a function of drain current; typical values



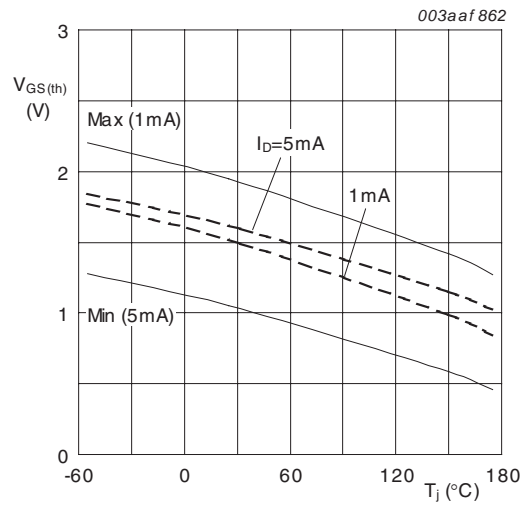
$V_{DS} = 10\text{V}$

Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values



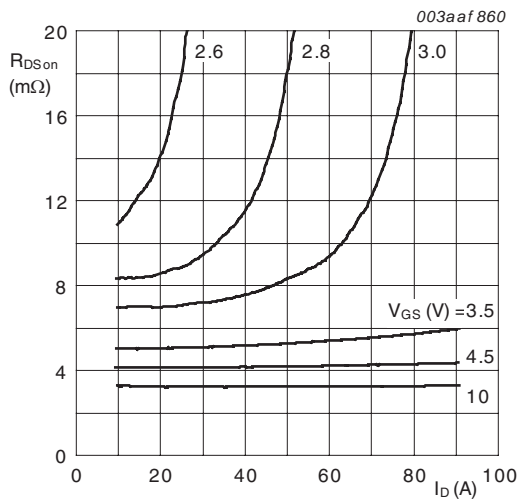
$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



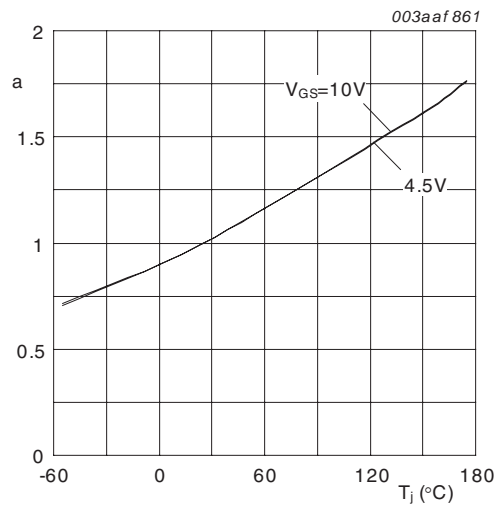
$V_{DS} = V_{GS}$

Fig 11. Gate-source threshold voltage as a function of junction temperature



$T_j = 25^\circ C$

Fig 12. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$

Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

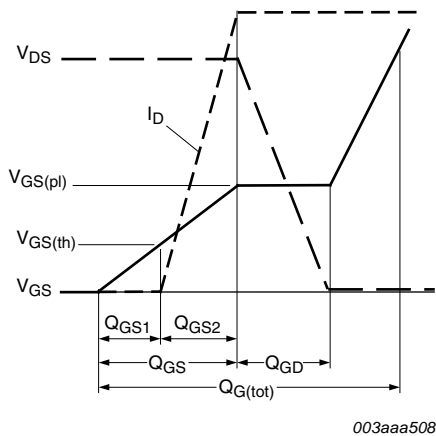
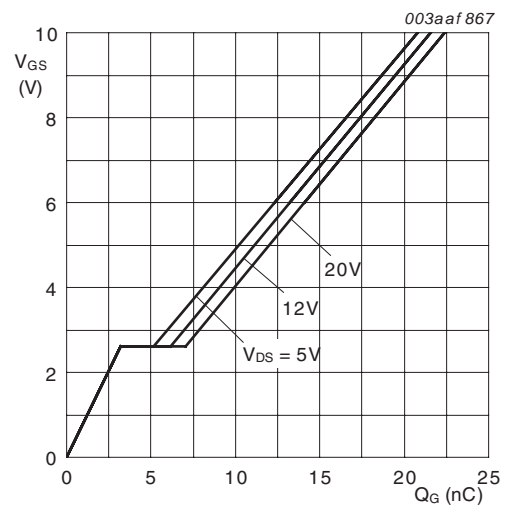
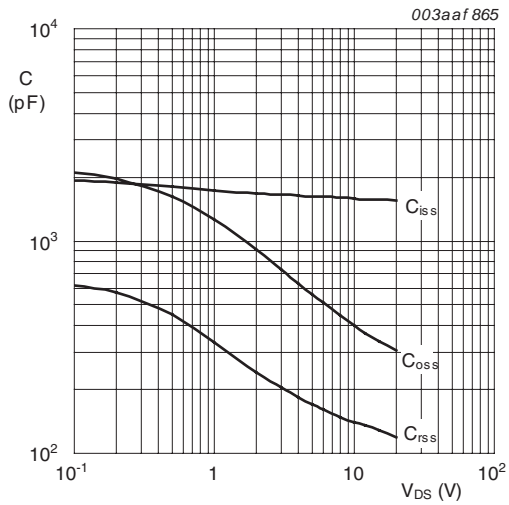


Fig 14. Gate charge waveform definitions



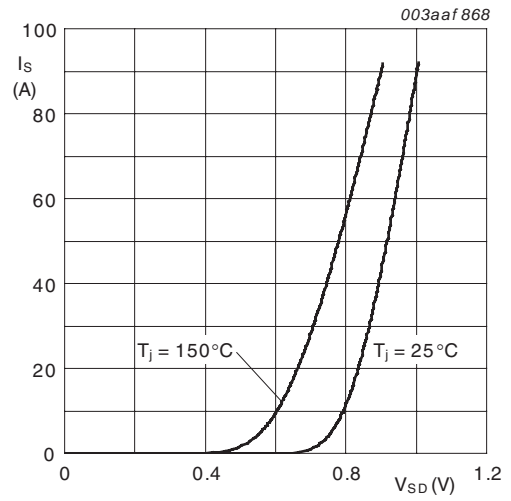
$T_j = 25^\circ C; I_D = 20A$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0V$

Fig 17. Source current as a function of source-drain voltage; typical values

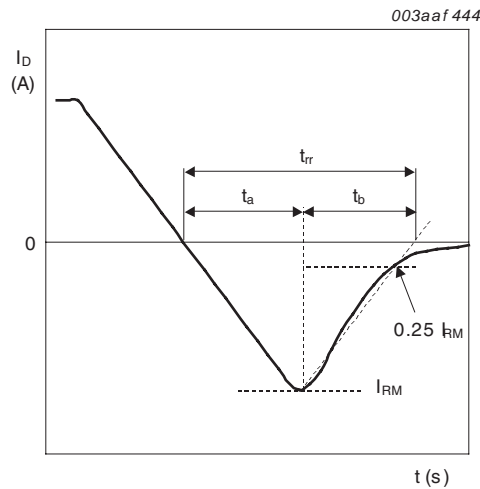


Fig 18. Reverse recovery timing definition

8. Package outline

Plastic single-ended surface-mounted package (LPAK; Power-SO8); 4 leads

SOT669



Fig 19. Package outline SOT669 (LPAK; Power-SO8)

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R7-25YLC v.1	20110502	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status ^[1] ^[2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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